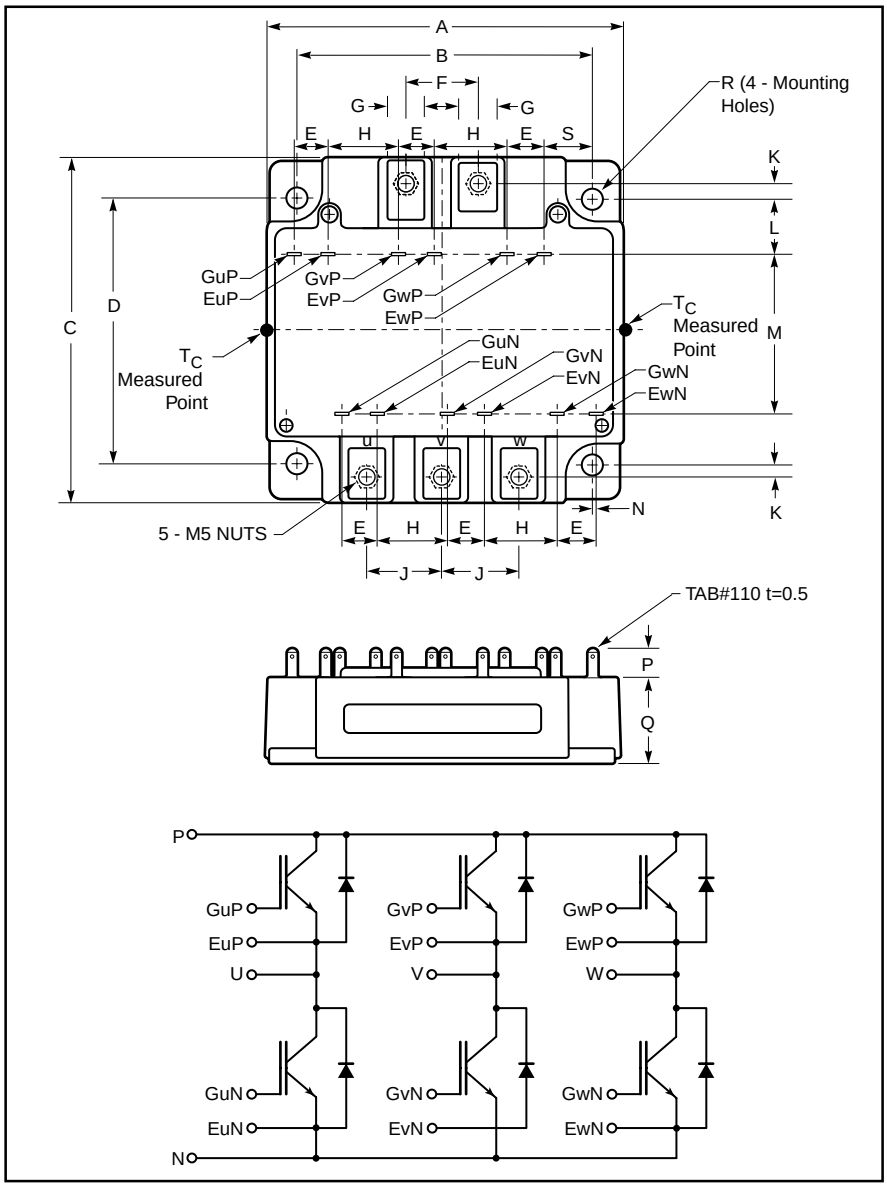
MITSUBISHI IGBT MODULES

CM200TU-12H

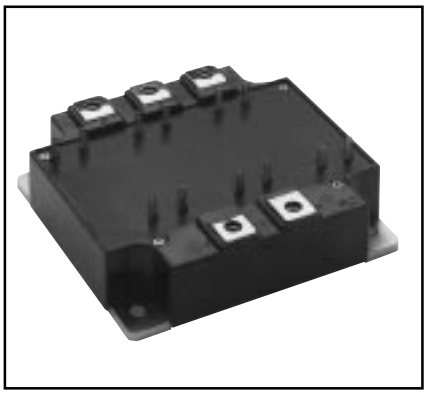
HIGH POWER SWITCHING USE
INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	3.54±0.01	90.0±0.25
C	4.02	102.0
D	3.15±0.01	80.0±0.25
E	0.43	11.0
F	0.91	23.0
G	0.47	12.0
H	0.85	21.7
J	0.91	23.0

Dimensions	Inches	Millimeters
K	0.15	3.75
L	0.67	17.0
M	1.91	48.5
N	0.03	0.8
P	0.32	8.1
Q	1.02	26.0
R	0.22 Dia.	5.5 Dia.
S	0.57	14.4



Description:
Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:
Example: Select the complete module number you desire from the table - i.e. CM200TU-12H is a 600V (V_{CES}), 200 Ampere Six-IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	200	12

MITSUBISHI ELECTRIC

CM200TU-12H

HIGH POWER SWITCHING USE
INSULATED TYPE

Absolute Maximum Ratings, T_j = 25 °C unless otherwise specified

Ratings	Symbol	CM200TU-12H	Units
Junction Temperature	T_j	-40 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	±20	Volts
Collector Current (T_c = 25°C)	I_C	200	Amperes
Peak Collector Current ($T_j \leq$ 150°C)	I_{CM}	400*	Amperes
Emitter Current**	I_E	200	Amperes
Peak Emitter Current**	I_{EM}	400*	Amperes
Maximum Collector Dissipation ($T_j <$ 150°C)	P_c	650	Watts
Mounting Torque, M5 Main Terminal	–	2.5~3.5	N · m
Mounting Torque, M5 Mounting	–	2.5~3.5	N · m
Weight	–	680	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Vrms

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.
**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_{GE} = 0V	–	–	1	mA
Gate Leakage Voltage	I_{GES}	$V_{GE} = V_{GES}$, V_{CE} = 0V	–	–	0.5	µA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	I_C = 15mA, V_{CE} = 10V	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 200A, V_{GE} = 15V, T_j = 25°C	–	2.4	3.0	Volts
		I_C = 200A, V_{GE} = 15V, T_j = 125°C	–	2.6	–	Volts
Total Gate Charge	Q_G	V_{CC} = 300V, I_C = 200A, V_{GE} = 15V	–	400	–	nC
Emitter-Collector Voltage*	V_{EC}	I_E = 200A, V_{GE} = 0V	–	–	2.6	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

Dynamic Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C_{ies}	V_{CE} = 10V, V_{GE} = 0V	–	–	17.6	nF
Output Capacitance		C_{oes}		–	–	9.6	nF
Reverse Transfer Capacitance		C_{res}		–	–	2.6	nF
Resistive	Turn-on Delay Time	$t_{d(on)}$	V_{CC} = 300V, I_C = 200A,	–	–	150	ns
Load	Rise Time	t_r	$V_{GE1} = V_{GE2}$ = 15V,	–	–	400	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	R_G = 3.1Ω, Resistive	–	–	300	ns
Times	Fall Time	t_f	Load Switching Operation	–	–	300	ns
Diode Reverse Recovery Time		t_{rr}	I_E = 200A, di_E/dt = -400A/µs	–	–	160	µC
Diode Reverse Recovery Charge		Q_{rr}	I_E = 200A, di_E/dt = -400A/µs	–	0.48	–	µC

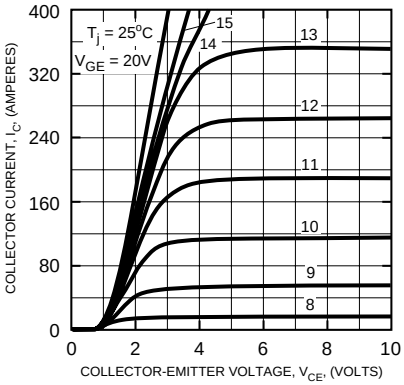
Thermal and Mechanical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}Q$	Per IGBT 1/6 Module	–	–	0.19	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}D$	Per Free-Wheel Diode 1/6 Module	–	–	0.35	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.015	–	°C/W

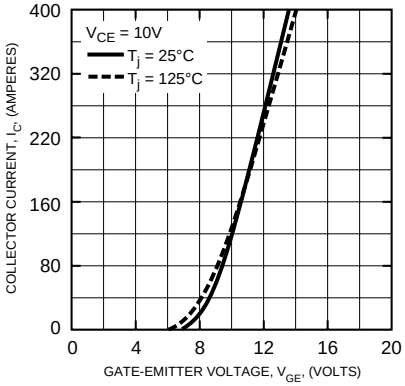
CM200TU-12H

HIGH POWER SWITCHING USE
INSULATED TYPE

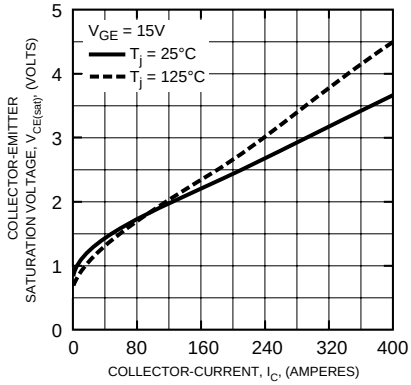
OUTPUT CHARACTERISTICS (TYPICAL)



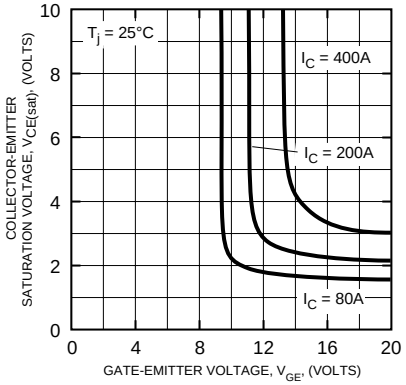
TRANSFER CHARACTERISTICS (TYPICAL)



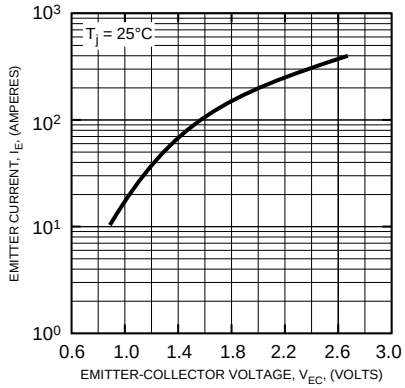
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



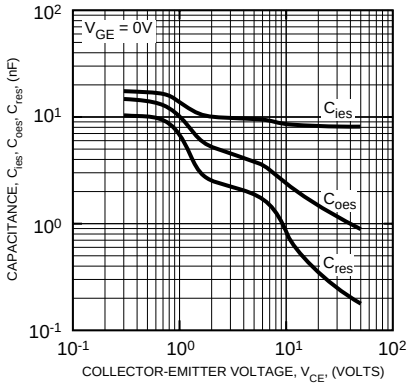
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



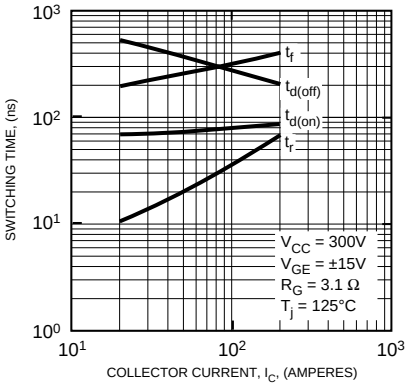
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



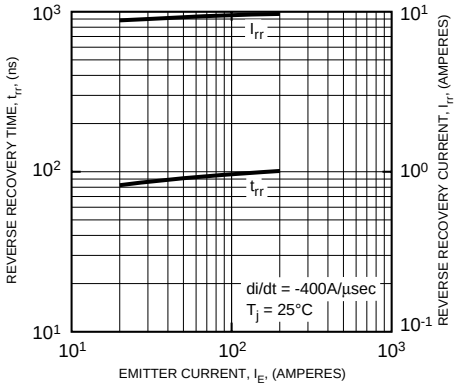
CAPACITANCE VS. V_{CE} (TYPICAL)



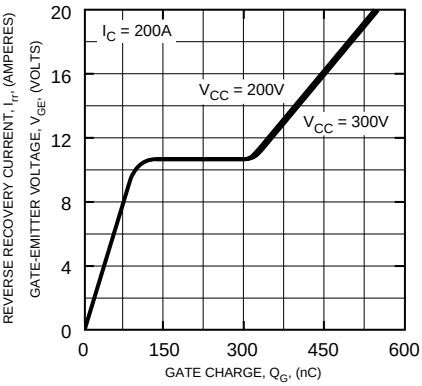
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



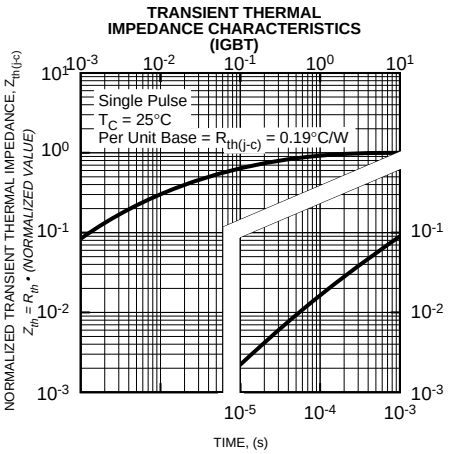
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

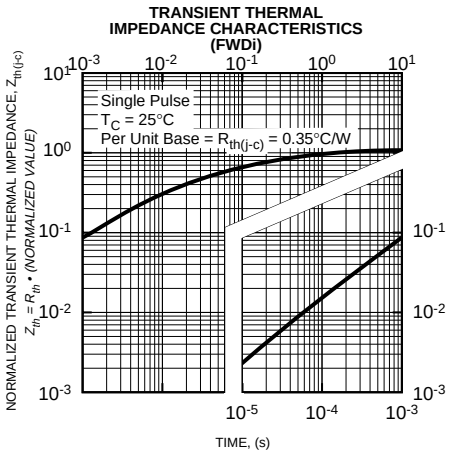


GATE CHARGE, V_{GE}



MITSUBISHI ELECTRIC


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT)
Single Pulse
T_C = 25°C
Per Unit Base = $R_{th(j-c)}$ = 0.19°C/W
NORMALIZED TRANSIENT THERMAL IMPEDANCE, $Z_{th(j-c)}$
$Z_{th} = R_{th} \bullet$ (NORMALIZED VALUE)
TIME, (s)


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi)
Single Pulse
T_C = 25°C
Per Unit Base = $R_{th(j-c)}$ = 0.35°C/W
NORMALIZED TRANSIENT THERMAL IMPEDANCE, $Z_{th(j-c)}$
$Z_{th} = R_{th} \bullet$ (NORMALIZED VALUE)
TIME, (s)